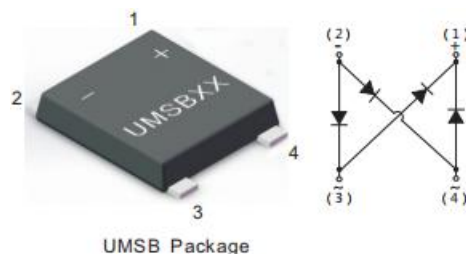


Bridge Rectifier Diode 整流桥

■Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Peak Soak Temperature 260℃ 峰值浸润温度 260 度
Package 封装: UMSB



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MSB50A	MSB50B	MSB50D	MSB50G	MSB50J	MSB50K	MSB50M	Unit 单位
Marking 印字		MB50A	MB50B	MB50D	MB50G	MB50J	MB50K	MB50M	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	5							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	150							A
Rating for Fusing 熔断值 (1ms < t < 8.3ms)	I^2t	93.375							A ² S
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	50							$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温和储藏温度	T_J, T_{stg}	$150^{\circ}\text{C}, -55\text{to}+150^{\circ}\text{C}$							

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F		1.1		V	$I_F=5\text{A}$
Reverse Current ($T_A=25^{\circ}\text{C}$) 反向电流($T_A=125^{\circ}\text{C}$)	I_R			5 200	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		60		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT
DERATING CURVE

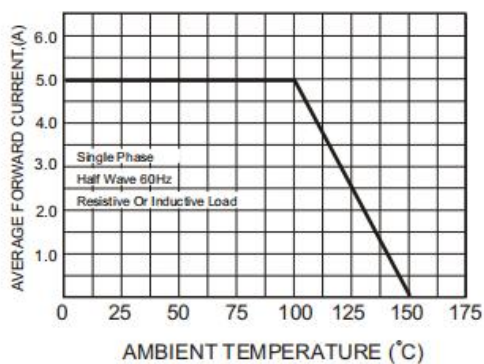


FIG.2-MAXIMUM NON-REPETITIVE FORWARD
SURGE CURRENT

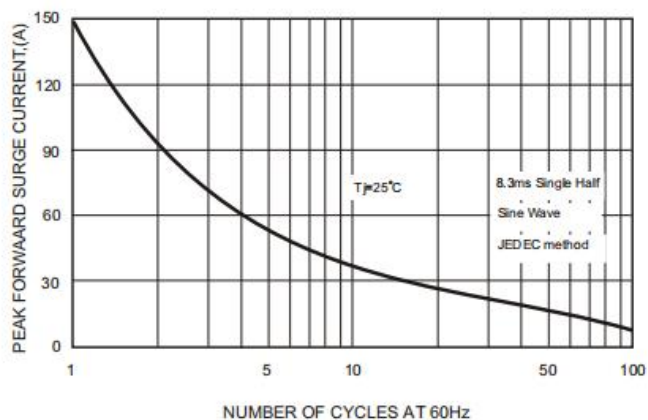


FIG.3-TYPICAL FORWARD
CHARACTERISTICS

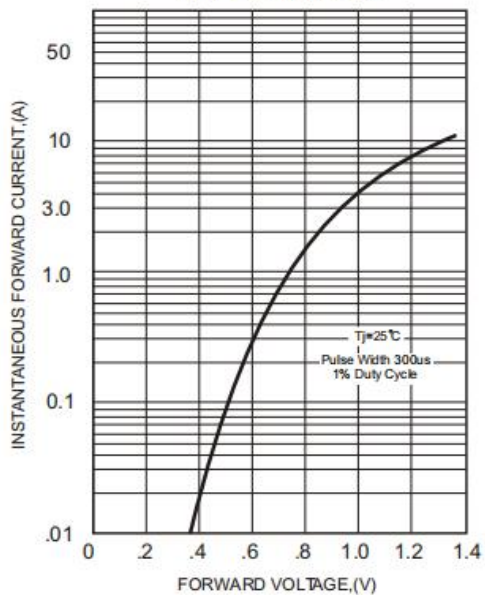
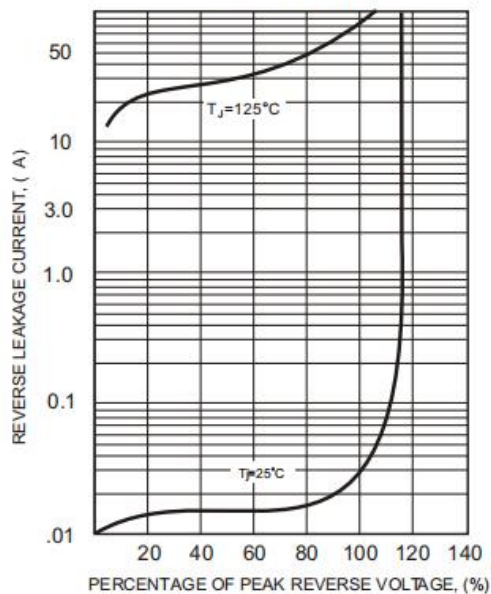
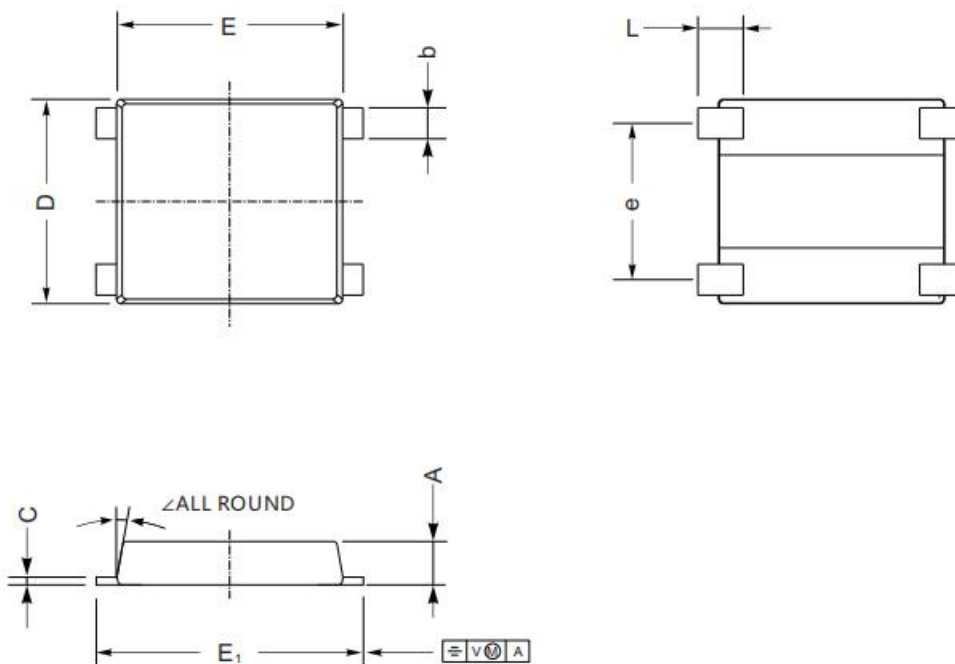


FIG.4-TYPICAL REVERSE
CHARACTERISTICS



■Dimension 外形封装尺寸



UMSB mechanical data

UNIT		A	C	D	E	E ₁	L	e	b	∠
mm	max	1.5	0.29	7.0	7.6	8.9	1.6	5.3	1.15	10°
	min	1.3	0.17	6.2	7.1	8.4	1.0	4.9	0.95	
mil	max	59	12	276	299	350	55	209	45	
	min	51	7	244	280	331	31.5	193	37	